

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|--------------------------------|---------------------|
| 1 | 2181 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 14:26 |
| 2 | 1702 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 14:27 |
| 4 | 35 | (TEOS or "tetra ethyl ortho silicate") same (implanted or implanting or implantation) same (boron or phosphorus) same (HF or vapor or hydrofluoric) same (contact or opening or trenches) and (resist or photoresist) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 14:31 |
| 5 | 1702 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 15:03 |
| 6 | 2065 | dual adj damascene | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 14:34 |
| 7 | 39 | ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist)) and (dual adj damascene) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 14:34 |
| 8 | 1 | | USPAT | 2003/07/22 14:38 |
| 9 | 1642 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 16:03 |
| 10 | 1184 | ((TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or vapor or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor) and 438/\$.ccls. | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 15:05 |
| 11 | 856 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 15:09 |
| 12 | 65 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor and (second adj opening) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 15:34 |
| 13 | 856 | (TEOS or "tetra ethyl ortho silicate") and (implanted or implanting or implantation) and (boron or phosphorus) and (HF or hydrofluoric) and (contact or opening or trenches) and (resist or photoresist) and etch\$3 and semiconductor | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 16:01 |

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|----|-----|--|--------------------------------|---------------------|
| 14 | 948 | (stacked or stack or stacking) same implant\$3 same (opening or contact or trenches) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 16:02 |
| 15 | 280 | ((stacked or stack or stacking) same implant\$3 same (opening or contact or trenches)) and (boron or phosphorus) and (HF or vapor) | USPAT; EPO; JPO; IBM_TDB | 2003/07/22 16:03 |